Jun Suda

List of Publications by Year
in descending order

Source: https://exaly.com/author-pdf/9599544/publications.pdf

Version: 2024-02-01

293	5,089	101543	155660
papers	citations	36 h-index	55 g-index

304	304	304	2781
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Breakdown Electric Field of GaN p⁺-n and p-n⁺Junction Diodes With Various Doping Concentrations. IEEE Electron Device Letters, 2022, 43, 96-99.	3.9	5
2	Dependence of Electrical Characteristics on Epitaxial Layer Structure of AlGaN/GaN HEMTs Fabricated on Freestanding GaN Substrates. IEEE Transactions on Electron Devices, 2022, 69, 88-95.	3.0	14
3	SiO₂/GaN interfaces with low defect densities and high breakdown electric fields formed by plasma-enhanced atomic layer deposition. Japanese Journal of Applied Physics, 2022, 61, SC1073.	1.5	11
4	Identification of type of threading dislocation causing reverse leakage in GaN pâ€“n junctions after continuous forward current stress. Scientific Reports, 2022, 12, 1458.	3.3	12
5	Hole traps related to nitrogen displacement in p-type GaN grown by metalorganic vapor phase epitaxy on freestanding GaN. Applied Physics Letters, 2022, 120, .	3.3	5
6	Effect of Ultraâ€Highâ€Pressure Annealing on Defect Reactions in Ionâ€Implanted GaN Studied by Positron Annihilation. Physica Status Solidi (B): Basic Research, 2022, 259, .	1.5	7
7	Impact of gamma-ray irradiation on capacitanceâ€“voltage characteristics of Al₂O₃/GaN MOS diodes with and without post-metallization annealing. Applied Physics Express, 2021, 14, 015501.	2.4	4
8	Design guidelines suppressing dynamic punch-through in GaN vertical MOSFETs by considering the Pooleâ€“Frenkel effect. Applied Physics Express, 2021, 14, 024001.	2.4	0
9	Fabrication of GaN cantilever on GaN substrate by photo-electrochemical etching. Applied Physics Express, 2021, 14, 036505.	2.4	5
10	Formation of highly vertical trenches with rounded corners via inductively coupled plasma reactive ion etching for vertical GaN power devices. Applied Physics Letters, 2021, 118, .	3.3	13
11	Mg-implanted bevel edge termination structure for GaN power device applications. Applied Physics Letters, 2021, 118, .	3.3	20
12	Isochronal annealing study of Mg-implanted p-type GaN activated by ultra-high-pressure annealing. Applied Physics Express, 2021, 14, 056501.	2.4	14
13	Impact ionization coefficients and critical electric field in GaN. Journal of Applied Physics, 2021, 129, .	2.5	55
14	Increase of reverse leakage current at homoepitaxial GaN p-n junctions induced by continuous forward current stress. Applied Physics Letters, 2021, 118, .	3.3	13
15	Design and demonstration of nearly-ideal edge termination for GaN pâ€“n junction using Mg-implanted field limiting rings. Applied Physics Express, 2021, 14, 074002.	2.4	19
16	Electrical characteristics of gatedâ€anode diodes based on normallyâ€off GaN HEMT structures for rectenna applications. Electronics Letters, 2021, 57, 810-812.	1.0	3
17	Photoionization cross section ratio of nitrogen-site carbon in GaN under sub-bandgap-light irradiation determined by isothermal capacitance transient spectroscopy. Applied Physics Express, 2021, 14, 091004.	2.4	3
18	Impact of channel mobility on design optimization of 600â€“3300ÂV-class high-speed GaN vertical-trench MOSFETs based on TCAD simulation. Applied Physics Express, 2021, 14, 094002.	2.4	5

#	Article	IF	Citations
19	Fabrication of 150â€nm AlGaN/GaN fieldâ€plated High Electron Mobility Transistors using i â€line stepper. Electronics Letters, 2021, 57, 948-949.	1.0	2
20	Depth profiles of electron traps generated during reactive ion etching in n-type 4H-SiC characterized by using isothermal capacitance transient spectroscopy. Journal of Applied Physics, 2021, 130, .	2.5	2
21	Analysis of intrinsic reverse leakage current resulting from band-to-band tunneling in dislocation-free GaN pâ€“n junctions. Applied Physics Express, 2021, 14, 114001.	2.4	11
22	Effects of the sequential implantation of Mg and N ions into GaN for p-type doping. Applied Physics Express, 2021, 14, 111001.	2.4	12
23	Nitrogen-displacement-related electron traps in n-type GaN grown on a GaN freestanding substrate. Applied Physics Letters, 2021, 118, .	3.3	24
24	Enhanced activation of Mg ion-implanted GaN at decreasing annealing temperature by prolonging duration. Applied Physics Express, 2021, 14, 011005.	2.4	17
25	Effect of annealing time and pressure on electrical activation and surface morphology of Mg-implanted GaN annealed at 1300 Â°C in ultra-high-pressure nitrogen ambient. Applied Physics Express, 2021, 14, 121004.	2.4	17
26	Effect of Schottky barrier height on quantitative analysis of deep-levels in n-type GaN by deep-level transient spectroscopy. AIP Advances, 2021, 11, 115124.	1.3	3
27	Effects of Dosage Increase on Electrical Properties of Metalâ€Oxideâ€Semiconductor Diodes with Mgâ€Ionâ€Implanted GaN Before Activation Annealing. Physica Status Solidi (B): Basic Research, 2020, 257, 1900367.	1.5	8
28	Overview of carrier compensation in GaN layers grown by MOVPE: toward the application of vertical power devices. Japanese Journal of Applied Physics, 2020, 59, SA0804.	1.5	39
29	Reduction of plasma-induced damage in n-type GaN by multistep-bias etching in inductively coupled plasma reactive ion etching. Applied Physics Express, 2020, 13, 016505.	2.4	20
30	Redistribution of Mg and H atoms in Mg-implanted GaN through ultra-high-pressure annealing. Applied Physics Express, 2020, 13, 086501.	2.4	30
31	Impact of Film Stress of Field-Plate Dielectric on Electric Characteristics of GaN-HEMTs. IEEE Transactions on Electron Devices, 2020, 67, 5421-5426.	3.0	14
32	Effects of ultra-high-pressure annealing on characteristics of vacancies in Mg-implanted GaN studied using a monoenergetic positron beam. Scientific Reports, 2020, 10, 17349.	3.3	22
33	Progress on and challenges of p-type formation for GaN power devices. Journal of Applied Physics, 2020, 128, .	2.5	54
34	Impacts of high temperature annealing above 1400Â° C under N2 overpressure to activate acceptors in Mg-implanted GaN. , 2020, , .		6
35	Electron traps formed by gamma-ray irradiation in homoepitaxial n-type GaN and their annealing behavior. AIP Advances, 2020, 10, 045023.	1.3	7
36	Identification of origin of E _C â€“0.6 eV electron trap level by correlation with iron concentration in n-type GaN grown on GaN freestanding substrate by metalorganic vapor phase epitaxy. Applied Physics Express, 2020, 13, 071007.	2.4	30

#	Article	IF	Citations
37	Defect evolution in Mg ions implanted GaN upon high temperature and ultrahigh N2 partial pressure annealing: Transmission electron microscopy analysis. Journal of Applied Physics, 2020, 127, .	2.5	38
38	Temperature Dependence of Conductivity Modulation in SiC Bipolar Junction Transistors. IEEE Transactions on Electron Devices, 2020, 67, 1699-1704.	3.0	5
39	Dual-color-sub-bandgap-light-excited isothermal capacitance transient spectroscopy for quick measurement of carbon-related hole trap density in n-type GaN. Japanese Journal of Applied Physics, 2020, 59, SGGD05.	1.5	7
40	Multi-cycle RHEED oscillation under nitrogen supply in alternative source supply AlN growth by rf-MBE. Applied Physics Express, 2020, 13, 025503.	2.4	2
41	Why do electron traps at E _C â€“0.6 eV have inverse correlation with carbon concentrations in n-type GaN layers?. Japanese Journal of Applied Physics, 2020, 59, 105505.	1.5	17
42	Depth profiling of surface damage in n-type GaN induced by inductively coupled plasma reactive ion etching using photo-electrochemical techniques. Applied Physics Express, 2020, 13, 106505.	2.4	6
43	Improvement of channel property of GaN vertical trench MOSFET by compensating nitrogen vacancies with nitrogen plasma treatment. Applied Physics Express, 2020, 13, 124003.	2.4	17
44	Estimation of Impact Ionization Coefficient in GaN by Photomulitiplication Measurement Utilizing Franz-Keldysh Effect. , 2019, , .		3
45	Shockleyâ€“Readâ€“Hall lifetime in homoepitaxial p-GaN extracted from recombination current in GaN pâ€“n⁺ junction diodes. Japanese Journal of Applied Physics, 2019, 58, SCCB14.	1.5	22
46	Deep-level transient spectroscopy studies of electron and hole traps in n-type GaN homoepitaxial layers grown by quartz-free hydride-vapor-phase epitaxy. Applied Physics Letters, 2019, 115, .	3.3	37
47	Franzâ€“Keldysh effect in 4H-SiC pâ€“n junction diodes under high electric field along the â©11$ar{{f{2}}}$0â direction. Japanese Journal of Applied Physics, 2019, 58, 091007.	1.5	2
48	Electric-field-induced simultaneous diffusion of Mg and H in Mg-doped GaN prepared using ultra-high-pressure annealing. Applied Physics Express, 2019, 12, 111005.	2.4	24
49	Demonstration of Conductivity Modulation in SiC Bipolar Junction Transistors With Reduced Base Spreading Resistance. IEEE Transactions on Electron Devices, 2019, 66, 4870-4874.	3.0	7
50	Acceptors activation of Mg-ion implanted GaN by ultra-high-pressure annealing. , 2019, , .		2
51	Highly effective activation of Mg-implanted p-type GaN by ultra-high-pressure annealing. Applied Physics Letters, 2019, 115, .	3.3	110
52	Measurement of avalanche multiplication utilizing Franz-Keldysh effect in GaN p-n junction diodes with double-side-depleted shallow bevel termination. Applied Physics Letters, 2019, 115, .	3.3	21
53	Design and Fabrication of GaN p-n Junction Diodes With Negative Beveled-Mesa Termination. IEEE Electron Device Letters, 2019, 40, 941-944.	3.9	78
54	Impact Ionization Coefficients in GaN Measured by Above- and Sub-E_g Illuminations for p^{â^’}/n⁺ Junction. , 2019, , .		22

#	Article	IF	Citations
55	Process Technologies for GaN High Voltage Devices. , 2019, , .		2
56	A comparative study on electrical characteristics of 1-kV pnp and npn SiC bipolar junction transistors. Japanese Journal of Applied Physics, 2018, 57, 04FR04.	1.5	3
57	Sources of carrier compensation in metalorganic vapor phase epitaxy-grown homoepitaxial n-type GaN layers with various doping concentrations. Applied Physics Express, 2018, 11, 041001.	2.4	59
58	Analytical formula for temperature dependence of resistivity in p-type 4H-SiC with wide-range doping concentrations. Japanese Journal of Applied Physics, 2018, 57, 088002.	1.5	5
59	Effects of Parasitic Region in SiC Bipolar Junction Transistors on Forced Current Gain. Materials Science Forum, 2018, 924, 629-632.	0.3	9
60	Determination of Surface Recombination Velocity From Currentâ€“Voltage Characteristics in SiC p-n Diodes. IEEE Transactions on Electron Devices, 2018, 65, 4786-4791.	3.0	6
61	Impacts of Finger Numbers on ON-State Characteristics in Multifinger SiC BJTs With Low Base Spreading Resistance. IEEE Transactions on Electron Devices, 2018, 65, 2771-2777.	3.0	5
62	Characterization of carrier concentration and mobility of GaN bulk substrates by Raman scattering and infrared reflectance spectroscopies. Japanese Journal of Applied Physics, 2018, 57, 070309.	1.5	1
63	Franz-Keldysh effect in GaN p-n junction diode under high reverse bias voltage. Applied Physics Letters, 2018, 112, .	3.3	18
64	Accurate method for estimating hole trap concentration in n-type GaN via minority carrier transient spectroscopy. Applied Physics Express, 2018, 11, 071002.	2.4	25
65	Phonon-assisted optical absorption due to Franzâ€“Keldysh effect in 4H-SiC pâ€“n junction diode under high reverse bias voltage. Applied Physics Express, 2018, 11, 091302.	2.4	7
66	Hall-effect measurements of metalorganic vapor-phase epitaxy-grown p-type homoepitaxial GaN layers with various Mg concentrations. Japanese Journal of Applied Physics, 2017, 56, 031001.	1.5	82
67	Temperature dependence of barrier height in Ni/n-GaN Schottky barrier diode. Applied Physics Express, 2017, 10, 051002.	2.4	40
68	Interface properties of NO-annealed 4H-SiC (0001), (112Â¯), and (11Â¯00) MOS structures with heavily doped p-bodies. Journal of Applied Physics, 2017, 121, .	2.5	11
69	Reduction of interface state density in SiC (0001) MOS structures by post-oxidation Ar annealing at high temperature. AIP Advances, 2017, 7, .	1.3	18
70	Effect of Postoxidation Nitridation on Forward Currentâ€“Voltage Characteristics in 4Hâ€“SiC Mesa p-n Diodes Passivated With SiO₂. IEEE Transactions on Electron Devices, 2017, 64, 3016-3018.	3.0	4
71	Electrical properties of n- and p-type 4H-SiC formed by ion implantation into high-purity semi-insulating substrates. Japanese Journal of Applied Physics, 2017, 56, 070306.	1.5	24
72	Design Criterion for SiC BJTs to Avoid ON-Characteristics Degradation Due to Base Spreading Resistance. IEEE Transactions on Electron Devices, 2017, 64, 2086-2091.	3.0	7

#	Article	IF	Citations
73	Ultrahigh-Voltage SiC MPS Diodes With Hybrid Unipolar/Bipolar Operation. IEEE Transactions on Electron Devices, 2017, 64, 874-881.	3.0	34
74	Correlation between shapes of Shockley stacking faults and structures of basal plane dislocations in 4H-SiC epilayers. Philosophical Magazine, 2017, 97, 2736-2752.	1.6	33
75	Characterization of lightly-doped n- and p-type homoepitaxial GaN on free-standing substrates. , 2017, , .		0
76	Analysis of quasi-ballistic hole transport capability of Ge and Si nanowire pMOSFETs by a quantum-corrected Boltzmann transport equation. , 2017, , .		1
77	Theoretical analysis of quasi-ballistic hole transport in Ge and Si nanowires focusing on energy relaxation process. , 2017, , .		0
78	Promise and Challenges of High-Voltage SiC Bipolar Power Devices. Energies, 2016, 9, 908.	3.1	31
79	Strain control in AlN top layer by inserting an ultrathin GaN interlayer on an AlN template coherently grown on SiC(0001) by PAMBE. Physica Status Solidi (B): Basic Research, 2016, 253, 814-818.	1.5	2
80	Hall-effect measurements of metalorganic vapor-phase epitaxy-grown p-type homoepitaxial GaN layers with various Mg concentrations. Japanese Journal of Applied Physics, 2016, 55, 05FH03.	1.5	2
81	Control of carrier lifetime of thick n-type 4H-SiC epilayers by high-temperature Ar annealing. Applied Physics Express, 2016, 9, 061303.	2.4	33
82	Impact of annealing temperature on surface passivation of SiC epitaxial layers with deposited SiO<inf>2</inf> followed by POCl<inf>3</inf> annealing. , 2016, , .		0
83	Interface state density of SiO2/p-type 4H-SiC (0001), (112Â¯), (11Â¯00) metal-oxide-semiconductor structures characterized by low-temperature subthreshold slopes. Applied Physics Letters, 2016, 108, .	3.3	31
84	Analysis of high-field hole transport in germanium and silicon nanowires based on Boltzmannâ€™s transport equation. IEEE Nanotechnology Magazine, 2016, , 1-1.	2.0	3
85	Analysis of ballistic and quasi-ballistic hole transport properties in germanium nanowires based on an extended â€œTop of the Barrierâ€•model. Solid-State Electronics, 2016, 123, 143-149.	1.4	3
86	Hall scattering factors in p-type 4H-SiC with various doping concentrations. Applied Physics Express, 2016, 9, 041301.	2.4	26
87	Surface passivation on 4H-SiC epitaxial layers by SiO₂ with POCl₃ annealing. Applied Physics Express, 2016, 9, 051301.	2.4	17
88	Franzâ€“Keldysh effect in n-type GaN Schottky barrier diode under high reverse bias voltage. Applied Physics Express, 2016, 9, 091002.	2.4	8
89	Theoretical analysis of high-field hole transport in germanium and silicon nanowires. , 2016, , .		0
90	Characterization of n-type and p-type GaN layers grown on free-standing GaN substrates. , 2016, , .		1

#	Article	IF	Citations
91	SiC and GaN from the viewpoint of vertical power devices. , 2016, , .		0
92	Modeling of surface roughness scattering in nanowires based on atomistic wave function: Application to hole mobility in rectangular germanium nanowires. Physical Review B, 2016, 93, .	3.2	5
93	Strong impact of the initial III/V ratio on the crystalline quality of an AlN layer grown by rf-plasma-assisted molecular-beam epitaxy. Applied Physics Express, 2016, 9, 025502.	2.4	7
94	Special issue on wide-bandgap semiconductor power electronics. Semiconductor Science and Technology, 2016, 31, 030301.	2.0	0
95	Oxidation-induced majority and minority carrier traps in n- and p-type 4H-SiC. Applied Physics Express, 2015, 8, 111301.	2.4	12
96	Temperature dependence of forward characteristics for ultrahigh-voltage SiC pâ€“iâ€“n diodes with a long carrier lifetime. Japanese Journal of Applied Physics, 2015, 54, 098004.	1.5	6
97	Temperature dependence of current gain in 4H-SiC bipolar junction transistors. Japanese Journal of Applied Physics, 2015, 54, 04DP13.	1.5	7
98	Interface Properties of 4H-SiC (<inline-formula> <tex-math notation="LaTeX">$11ar {2}0$) Tj ETQq0 0 0 rgBT /Overlock 10 Tf in NO. IEEE Transactions on Electron Devices, 2015, 62, 309-315.	3.0	74
99	Impacts of orientation and cross-sectional shape on hole mobility of Si nanowire MOSFETs. , 2015, , .		0
100	Impact Ionization Coefficients in 4H-SiC Toward Ultrahigh-Voltage Power Devices. IEEE Transactions on Electron Devices, 2015, 62, 3326-3333.	3.0	70
101	Influence of Conduction-Type on Thermal Oxidation Rate in SiC(0001) with Various Doping Densities. Materials Science Forum, 2015, 821-823, 456-459.	0.3	1
102	Ultrahigh-Voltage SiC p-i-n Diodes With Improved Forward Characteristics. IEEE Transactions on Electron Devices, 2015, 62, 374-381.	3.0	110
103	Impact of conduction type and doping density on thermal oxidation rate of SiC(0001). Applied Physics Express, 2014, 7, 121301.	2.4	5
104	Effect of ultrathin AlN spacer on electronic properties of GaN/SiC heterojunction bipolar transistors. Japanese Journal of Applied Physics, 2014, 53, 034101.	1.5	16
105	Orientation and size effects on phonon-limited hole mobility in rectangular cross-sectional germanium nanowires. , 2014, , .		0
106	Quantitative comparison between Z1â^•2 center and carbon vacancy in 4H-SiC. Journal of Applied Physics, 2014, 115, .	2.5	39
107	Conduction-type dependence of thermal oxidation rate on SiC(0001). , 2014, , .		1
108	Etching-limiting process and origin of loading effects in silicon etching with hydrogen chloride gas. Japanese Journal of Applied Physics, 2014, 53, 016502.	1.5	2

#	Article	IF	Citations
109	Fabrication of Electrostatically Actuated 4H-SiC Microcantilever Resonators by Using n/p/n Epitaxial Structures and Doping-Selective Electrochemical Etching. Materials Science Forum, 2014, 778-780, 780-783.	0.3	2
110	Enhancement of carrier lifetime in lightly Al-doped p-type 4H-SiC epitaxial layers by combination of thermal oxidation and hydrogen annealing. Applied Physics Express, 2014, 7, 085501.	2.4	28
111	Temperature dependence of optical absorption coefficient of 4H- and 6H-SiC from room temperature to 300 Â°C. Japanese Journal of Applied Physics, 2014, 53, 108003.	1.5	20
112	Phonon-Limited Electron Mobility in Rectangular Cross-Sectional Ge Nanowires. IEEE Transactions on Electron Devices, 2014, 61, 1993-1998.	3.0	11
113	100 mm diameter mono-crystalline 4H-SiC/polycrystalline-SiC bonded wafers fabricated by SAB for power device. , 2014, , .		1
114	4H-SiC MISFETs With 4H-AlN Gate Insulator Isopolytypically Grown on 4H-SiC $(11ar{2}0)$. IEEE Electron Device Letters, 2014, 35, 339-341.	3.9	11
115	Decay curve analyses in carrier lifetime measurements of p- and n-type 4H-SiC epilayers. Japanese Journal of Applied Physics, 2014, 53, 111301.	1.5	6
116	Identification of dislocations in 4H-SiC epitaxial layers and substrates using photoluminescence imaging. Japanese Journal of Applied Physics, 2014, 53, 020304.	1.5	30
117	Ion implantation technology in SiC for power device applications. , 2014, , .		20
118	Formation mechanism of threading-dislocation array in AlN layers grown on 6H-SiC (0001) substrates with 3-bilayer-high surface steps. Applied Physics Letters, 2014, 105, .	3.3	14
119	Orientation and Shape Effects on Ballistic Transport Properties in Gate-All-Around Rectangular Germanium Nanowire nFETs. IEEE Transactions on Electron Devices, 2013, 60, 944-950.	3.0	11
120	AlGaN/SiC Heterojunction Bipolar Transistors Featuring AlN/GaN Short-Period Superlattice Emitter. IEEE Transactions on Electron Devices, 2013, 60, 2768-2775.	3.0	5
121	Size and geometric effects on conduction band structure of GaAs nanowires. , 2013, , .		0
122	Deep levels generated by thermal oxidation in p-type 4H-SiC. Journal of Applied Physics, 2013, 113, .	2.5	18
123	Coherent Growth of AlN/GaN Short-Period Superlattice with Average GaN Mole Fraction of up to 20% on 6H-SiC(0001) Substrates by Plasma-Assisted Molecular-Beam Epitaxy. Japanese Journal of Applied Physics, 2013, 52, 08JE21.	1.5	4
124	Effects of Nitridation on 4H-SiC MOSFETs Fabricated on Various Crystal Faces. IEEE Transactions on Electron Devices, 2013, 60, 1260-1262.	3.0	61
125	Single-crystalline 4H-SiC micro cantilevers with a high quality factor. Sensors and Actuators A: Physical, 2013, 197, 122-125.	4.1	20
126	Junction technology in SiC for high-voltage power devices. , 2013, , .		0

#	Article	IF	Citations
127	Long Photoconductivity Decay Characteristics in p-Type 4H-SiC Bulk Crystals. Japanese Journal of Applied Physics, 2013, 52, 010202.	1.5	9
128	Optical Properties of Highly Strained AlN Coherently Grown on 6H-SiC(0001). Applied Physics Express, 2013, 6, 062604.	2.4	12
129	Improvement of Carrier Lifetimes in Highly Al-Doped p-Type 4H-SiC Epitaxial Layers by Hydrogen Passivation. Applied Physics Express, 2013, 6, 121301.	2.4	24
130	Ultrahigh-Voltage SiC PiN Diodes with an Improved Junction Termination Extension Structure and Enhanced Carrier Lifetime. Japanese Journal of Applied Physics, 2013, 52, 070204.	1.5	6
131	Deep Levels Generated by Thermal Oxidation in n-Type 4H-SiC. Applied Physics Express, 2013, 6, 051301.	2.4	14
132	Growth, Electrical Characterization, and Electroluminescence of GaN/SiC Heterojunction Diodes and Bipolar Transistors Fabricated on SiC Off-Axis Substrates. Japanese Journal of Applied Physics, 2013, 52, 124102.	1.5	2
133	Investigation on origin of Z1/2 center in SiC by deep level transient spectroscopy and electron paramagnetic resonance. Applied Physics Letters, 2013, 102, .	3.3	56
134	Over-700-nm Critical Thickness of AlN Grown on 6H-SiC(0001) by Molecular Beam Epitaxy. Applied Physics Express, 2012, 5, 105502.	2.4	26
135	AlN/GaN Short-Period Superlattice Coherently Grown on 6H-SiC(0001) Substrates by Molecular Beam Epitaxy. Applied Physics Express, 2012, 5, 051002.	2.4	3
136	Enhanced Current Gain (>250) in 4H-SiC Bipolar Junction Transistors by a Deep-Level-Reduction Process. Materials Science Forum, 2012, 717-720, 1117-1122.	0.3	9
137	Experimental Study on Various Junction Termination Structures Applied to 15 kV 4H-SiC PiN Diodes. Materials Science Forum, 2012, 717-720, 973-976.	0.3	4
138	Elimination of Deep Levels in Thick SiC Epilayers by Thermal Oxidation and Proposal of the Analytical Model. Materials Science Forum, 2012, 717-720, 241-246.	0.3	6
139	21.7 kV 4H-SiC PiN Diode with a Space-Modulated Junction Termination Extension. Applied Physics Express, 2012, 5, 064001.	2.4	67
140	Carrier Recombination in n-Type 4H-SiC Epilayers with Long Carrier Lifetimes. Applied Physics Express, 2012, 5, 101301.	2.4	55
141	Current Transport Characteristics of Quasi-Al$_{x}$Ga$_{1-x}$N/SiC Heterojunction Bipolar Transistors with Various Band Discontinuities. Japanese Journal of Applied Physics, 2012, 51, 04DP09.	1.5	1
142	Growth of Nitrogen-Polar 2H-AlN on Step-Height-Controlled 6H-SiC(0001Ì„) Substrate by Molecular-Beam Epitaxy. Japanese Journal of Applied Physics, 2012, 51, 02BH02.	1.5	1
143	High temperature annealing of n-type 4H-SiC: Impact on intrinsic defects and carrier lifetime. Journal of Applied Physics, 2012, 111, .	2.5	58
144	4H-SiC pn Photodiodes with Temperature-Independent Photoresponse up to 300 ^{circ}C. Applied Physics Express, 2012, 5, 094101.	2.4	25

#	Article	IF	Citations
145	Analytical model for reduction of deep levels in SiC by thermal oxidation. Journal of Applied Physics, 2012, 111, .	2.5	69
146	Breakdown characteristics of 12–20 kV-class 4H-SiC PiN diodes with improved junction termination structures. , 2012, , .		14
147	Fundamental study on junction termination structures for ultrahigh-voltage SiC PiN diodes. , 2012, , .		2
148	21-kV SiC BJTs With Space-Modulated Junction Termination Extension. IEEE Electron Device Letters, 2012, 33, 1598-1600.	3.9	96
149	Thermo-Optic Coefficients of 4H-SiC, GaN, and AlN for Ultraviolet to Infrared Regions up to 500 Â°C. Japanese Journal of Applied Physics, 2012, 51, 112101.	1.5	16
150	Breakdown Characteristics of 15-kV-Class 4H-SiC PiN Diodes With Various Junction Termination Structures. IEEE Transactions on Electron Devices, 2012, 59, 2748-2752.	3.0	36
151	Orientation and size effects on ballistic electron transport properties in gate-all-around rectangular germanium nanowire FETs. , 2012, , .		0
152	Space-Modulated Junction Termination Extension for Ultrahigh-Voltage p-i-n Diodes in 4H-SiC. IEEE Transactions on Electron Devices, 2012, 59, 414-418.	3.0	87
153	Growth of Nitrogen-Polar 2H-AlN on Step-Height-Controlled 6H-SiC(0001Ì„) Substrate by Molecular-Beam Epitaxy. Japanese Journal of Applied Physics, 2012, 51, 02BH02.	1.5	3
154	Current Transport Characteristics of Quasi-AlxGa1-xN/SiC Heterojunction Bipolar Transistors with Various Band Discontinuities. Japanese Journal of Applied Physics, 2012, 51, 04DP09.	1.5	1
155	Thermo-Optic Coefficients of 4H-SiC, GaN, and AlN for Ultraviolet to Infrared Regions up to 500 Â°C. Japanese Journal of Applied Physics, 2012, 51, 112101.	1.5	12
156	4H-SiC BJTs With Record Current Gains of 257 on (0001) and 335 on ($ hbox{000}ar{hbox{1}}$). IEEE Electron Device Letters, 2011, 32, 841-843.	3.9	46
157	Improvement of Current Gain in 4H-SiC BJTs by Surface Passivation With Deposited Oxides Nitrided in $hbox{N}_{2}hbox{O}$ or NO. IEEE Electron Device Letters, 2011, 32, 285-287.	3.9	33
158	Epitaxial Growth and Defect Control of SiC for High-Voltage Power Devices. Journal of the Vacuum Society of Japan, 2011, 54, 362-368.	0.3	2
159	Thermo-optic coefficients of SiC, GaN, and AlN up to 512Â°C from infrared to ultraviolet region for tunable filter applications. Proceedings of SPIE, 2011, , .	0.8	3
160	Fabrication of electrostatic-actuated single-crystalline 4H-SiC bridge structures by photoelectrochemical etching. Proceedings of SPIE, 2011, , .	0.8	6
161	Anomalously low Ga incorporation in high Al-content AlGaN grown on $(11{ar {2}}0)$ non-polar plane by molecular beam epitaxy. Physica Status Solidi (A) Applications and Materials Science, 2011, 208, 1498-1500.	1.8	2
162	Reliability of Nitrided Gate Oxides for N- and P-Type 4H-SiC(0001) Metalâ€“Oxideâ€“Semiconductor Devices. Japanese Journal of Applied Physics, 2011, 50, 090201.	1.5	3

#	Article	IF	Citations
163	Origin of Etch Hillocks Formed on On-Axis SiC(0001) Surfaces by Molten KOH Etching. Japanese Journal of Applied Physics, 2011, 50, 038002.	1.5	6
164	Nonradiative recombination at threading dislocations in 4H-SiC epilayers studied by micro-photoluminescence mapping. Journal of Applied Physics, 2011, 110, .	2.5	27
165	4H-SiC bipolar junction transistors with record current gains of 257 on (0001) and 335 on (000–1). , 2011, , .		11
166	Reduction of Threading Dislocation Density in 2H-AlN Grown on 6H-SiC(0001) by Minimizing Unintentional Active-Nitrogen Exposure before Growth. Applied Physics Express, 2011, 4, 025502.	2.4	29
167	Improved Current Gain in 4H-SiC BJTs Passivated with Deposited Oxides Followed by Nitridation. Materials Science Forum, 2011, 679-680, 698-701.	0.3	0
168	Bandgap shift by quantum confinement effect in ã€˜100ã€‰ Si-nanowires derived from threshold-voltage shift of fabricated metal-oxide-semiconductor field effect transistors and theoretical calculations. Journal of Applied Physics, 2011, 109, 064312.	2.5	6
169	Quantum-confinement effect on holes in silicon nanowires: Relationship between wave function and band structure. Journal of Applied Physics, 2011, 109, 064318.	2.5	16
170	Reliability of Nitrided Gate Oxides for N- and P-Type 4H-SiC(0001) Metalâ€“Oxideâ€“Semiconductor Devices. Japanese Journal of Applied Physics, 2011, 50, 090201.	1.5	9
171	Origin of Etch Hillocks Formed on On-Axis SiC(0001) Surfaces by Molten KOH Etching. Japanese Journal of Applied Physics, 2011, 50, 038002.	1.5	2
172	Nearly Ideal Currentâ€“Voltage Characteristics of Schottky Barrier Diodes Formed on Hydride-Vapor-Phase-Epitaxy-Grown GaN Free-Standing Substrates. Applied Physics Express, 2010, 3, 101003.	2.4	124
173	Enhancement of Carrier Lifetimes in n-Type 4H-SiC Epitaxial Layers by Improved Surface Passivation. Applied Physics Express, 2010, 3, 121201.	2.4	26
174	Sources of Epitaxial Growth-Induced Stacking Faults in 4H-SiC. Journal of Electronic Materials, 2010, 39, 1166-1169.	2.2	13
175	Enhancement of initial layer-by-layer growth and reduction of threading dislocation density by optimized Ga pre-irradiation in molecular-beam epitaxy of 2H-AlN on 6H-SiC(0001). Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 2094-2096.	0.8	14
176	Wide-bandgap Semiconductor Devices using Group-III Nitride/SiC Heterointerface. Hyomen Kagaku, 2010, 31, 651-656.	0.0	1
177	Non-destructive Detection and Visualization of Extended Defects in 4H-SiC Epilayers. Materials Research Society Symposia Proceedings, 2010, 1246, 1.	0.1	0
178	Nonpolar 4H-Polytype AlN/AlGaN Multiple Quantum Well Structure Grown on 4H-SiC(1ar100). Applied Physics Express, 2010, 3, 051001.	2.4	6
179	Reduction of deep levels generated by ion implantation into n- and p-type 4Hâ€“SiC. Journal of Applied Physics, 2010, 108, .	2.5	33
180	Deep levels induced by reactive ion etching in n- and p-type 4Hâ€“SiC. Journal of Applied Physics, 2010, 108, 023706.	2.5	33

#	Article	IF	Citations
181	Impacts of recombination at the surface and in the substrate on carrier lifetimes of n-type 4Hâ€“SiC epilayers. Journal of Applied Physics, 2010, 108, 083721.	2.5	72
182	Influence of Effective Fixed Charges on Short-Channel Effects in SiC Metalâ€“Oxideâ€“Semiconductor Field-Effect Transistors. Japanese Journal of Applied Physics, 2010, 49, 024204.	1.5	3
183	Nondestructive Visualization of Individual Dislocations in 4H-SiC Epilayers by Micro Photoluminescence Mapping. Japanese Journal of Applied Physics, 2010, 49, 090201.	1.5	8
184	Accurate measurement of quadratic nonlinear-optical coefficients of gallium nitride. Journal of the Optical Society of America B: Optical Physics, 2010, 27, 2026.	2.1	21
185	Tight-binding study of size and geometric effects on hole effective mass of silicon nanowires. , 2010, , .		0
186	Demonstration of Commonâ€“Emitter Operation in AlGaN/SiC Heterojunction Bipolar Transistors. IEEE Electron Device Letters, 2010, 31, 942-944.	3.9	11
187	1580-Vâ€“40-$hbox{m}Omegacdot hbox{cm}^{2}$ Double-RESURF MOSFETs on 4H-SiC$(hbox{000}ar{hbox{1}})$. IEEE Electron Device Letters, 2009, 30, 831-833.	3.9	40
188	Triple Shockley type stacking faults in 4H-SiC epilayers. Applied Physics Letters, 2009, 94, .	3.3	66
189	Polytype Replication in Heteroepitaxial Growth of Nonpolar AlN on SiC. MRS Bulletin, 2009, 34, 348-352.	3.5	7
190	Systematic Investigation ofc-Axis Tilt in GaN and AlGaN Grown on Vicinal SiC(0001) Substrates. Japanese Journal of Applied Physics, 2009, 48, 020202.	1.5	8
191	In situGravimetric Monitoring of Thermal Decomposition and Hydrogen Etching Rates of 6H-SiC(0001) Si Face. Japanese Journal of Applied Physics, 2009, 48, 095505.	1.5	5
192	Electrostatic-Actuated Suspended Ribbon Structure Fabricated in Single-Crystalline SiC by Selective Photoelectrochemical Etching. Japanese Journal of Applied Physics, 2009, 48, 111101.	1.5	2
193	Mobility oscillation by one-dimensional quantum confinement in Si-nanowire metal-oxide-semiconductor field effect transistors. Journal of Applied Physics, 2009, 106, 034312.	2.5	10
194	High Channel Mobility in P-Channel MOSFETs Fabricated on 4H-SiC (0001) and Non-Basal Faces. Materials Science Forum, 2009, 615-617, 789-792.	0.3	0
195	Spatial Profiling of Planar Defects in 4H-SiC Epilayers Using Micro-Photoluminescence Mapping. Materials Science Forum, 2009, 615-617, 245-250.	0.3	1
196	Anomalously Large Difference in Ga Incorporation for AlGaN Grown on the (11ar20) and (1ar100) Planes under Group-III-Rich Conditions. Applied Physics Express, 2009, 2, 091003.	2.4	3
197	P-Channel MOSFETs on 4H-SiC {0001} and Nonbasal Faces Fabricated by Oxide Deposition and $hbox{N}_{2}hbox{O}$ Annealing. IEEE Transactions on Electron Devices, 2009, 56, 1953-1958.	3.0	45
198	Enhanced Drain Current of 4H-SiC MOSFETs by Adopting a Three-Dimensional Gate Structure. IEEE Transactions on Electron Devices, 2009, 56, 2632-2637.	3.0	12

#	Article	IF	Citations
199	Observation of novel defect structure in 2H-AlN grown on 6H-SiC(0001) substrates with 3-bilayer-height step-and-terrace structures. Physica Status Solidi (A) Applications and Materials Science, 2009, 206, 1187-1189.	1.8	5
200	4Hâ€SiC MISFETs with nitrogenâ€containing insulators. Physica Status Solidi (A) Applications and Materials Science, 2009, 206, 2374-2390.	1.8	70
201	Determination of the thermoâ€optic coefficients of GaN and AlN up to 515 Â°C. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S776.	0.8	2
202	Characterization of major in-grown stacking faults in 4H-SiC epilayers. Physica B: Condensed Matter, 2009, 404, 4745-4748.	2.7	59
203	Accurate measurements of second-order nonlinear optical coefficients of 6H and 4H silicon carbide. Journal of the Optical Society of America B: Optical Physics, 2009, 26, 1892.	2.1	48
204	Temperature and doping dependencies of electrical properties in Al-doped 4H-SiC epitaxial layers. Journal of Applied Physics, 2009, 106, .	2.5	89
205	Demonstration of SiC heterojunction bipolar transistors with AlN/GaN short-period superlattice widegap emitter. , 2009, , .		1
206	A New Class of Step-and-Terrace Structure Observed on 4H-SiC(0001) after High-Temperature Gas Etching. Applied Physics Express, 2009, 2, 101603.	2.4	3
207	Lifetimeâ€killing defects in 4Hâ€SiC epilayers and lifetime control by lowâ€energy electron irradiation. Physica Status Solidi (B): Basic Research, 2008, 245, 1327-1336.	1.5	112
208	Simulation and Experimental Study on the Junction Termination Structure for High-Voltage 4H-SiC PiN Diodes. IEEE Transactions on Electron Devices, 2008, 55, 1841-1846.	3.0	73
209	4H-SiC MIS Capacitors and MISFETs With Deposited $hbox{SiN}_{x}/ hbox{SiO}_{2}$ Stack-Gate Structures. IEEE Transactions on Electron Devices, 2008, 55, 2054-2060.	3.0	18
210	The temperature dependence of the refractive indices of GaN and AlN from room temperature up to 515â€‰Â°C. Journal of Applied Physics, 2008, 104, .	2.5	90
211	Comprehensive analysis of multiple-reflection effects on rotational Maker-fringe experiments. Journal of the Optical Society of America B: Optical Physics, 2008, 25, 1616.	2.1	11
212	4H-SiC Double RESURF MOSFETs with a Record Performance by Increasing RESURF Dose. , 2008, , .		4
213	Fabrication and Electronic Characteristics of Silicon Nanowire MOSFETs. Materials Research Society Symposia Proceedings, 2008, 1080, 1.	0.1	0
214	N 2 O -grown oxides/4H-SiC (0001), (033Â¯8), and (112Â¯) interface properties characterized by using p-type gate-controlled diodes. Applied Physics Letters, 2008, 93, .	3.3	9
215	Temperature Dependence of Electrical Properties of NiO Thin Films for Resistive Random Access Memory. Materials Research Society Symposia Proceedings, 2008, 1071, 1.	0.1	2
216	Enhanced Channel Mobility in 4H-SiC MISFETs by Utilizing Deposited SiN/SiO₂ Stack Gate Structures. Materials Science Forum, 2008, 600-603, 679-682.	0.3	9

#	Article	IF	Citations
217	Improvement of Channel Mobility in Inversion-Type n-Channel GaN Metalâ€“Oxideâ€“Semiconductor Field-Effect Transistor by High-Temperature Annealing. Japanese Journal of Applied Physics, 2008, 47, 7784.	1.5	35
218	Hydrogen Implantation and Annealing-Induced Exfoliation Process in SiC Wafers with Various Crystal Orientations. Japanese Journal of Applied Physics, 2008, 47, 5352.	1.5	4
219	Surface Morphologies of 4H-SiC(11ar20) and (1ar100) Treated by High-Temperature Gas Etching. Japanese Journal of Applied Physics, 2008, 47, 8388-8390.	1.5	6
220	Characterization of stacking faults in 4H-SiC epilayers by room-temperature microphotoluminescence mapping. Applied Physics Letters, 2008, 92, 221906.	3.3	101
221	Nonpolar 4H-AlN grown on 4H-SiC (11Â¯00) with reduced stacking fault density realized by persistent layer-by-layer growth. Applied Physics Letters, 2008, 93, 082106.	3.3	9
222	Improved Performance of 4H-SiC Double Reduced Surface Field Metalâ€“Oxideâ€“Semiconductor Field-Effect Transistors by Increasing RESURF Doses. Applied Physics Express, 2008, 1, 101403.	2.4	9
223	Impact of Acceptor Concentration on Electronic Properties of n⁺-GaN/p⁺-SiC Heterojunction for GaN/SiC Heterojunction Bipolar Transistor. Materials Science Forum, 2007, 556-557, 1039-1042.	0.3	5
224	Lateral 4H-SiC MOSFETs with Low On-Resistance by Using Two-Zone Double RESURF Structure. Materials Science Forum, 2007, 556-557, 815-818.	0.3	0
225	4Hâ€“SiC Lateral Double RESURF MOSFETs With Low on Resistance. IEEE Transactions on Electron Devices, 2007, 54, 1216-1223.	3.0	40
226	Accurate Determination of Nonlinear Optical Coefficients of Hexagonal Silicon Carbide of Polytype 6H. , 2007, , .		0
227	Structure Analysis of ZrB2(0001) Surface Prepared byex situHF Treatment. Japanese Journal of Applied Physics, 2006, 45, L497-L500.	1.5	5
228	Electron Injection from GaN to SiC and Fabrication of GaN/SiC Heterojunction Bipolar Transistors. Materials Science Forum, 2006, 527-529, 1545-1548.	0.3	7
229	Reduction of On-Resistance in 4H-SiC Multi-RESURF MOSFETs. Materials Science Forum, 2006, 527-529, 1305-1308.	0.3	1
230	Low-dislocation-density Nonpolar AlN Grown on 4H-SiC (11-20) Substrates. Materials Research Society Symposia Proceedings, 2006, 955, 1.	0.1	0
231	Improved Dielectric and Interface Properties of 4H-SiC MOS Structures Processed by Oxide Deposition and N₂O Annealing. Materials Science Forum, 2006, 527-529, 987-990.	0.3	29
232	Anisotropic etching of single crystalline SiC using molten KOH for SiC bulk micromachining. , 2006, , .		5
233	High-quality nonpolar 4H-AlN grown on 4H-SiC (112Â¯0) substrate by molecular-beam epitaxy. Applied Physics Letters, 2006, 89, 112117.	3.3	37
234	Experimental and Theoretical Investigations on Short-Channel Effects in 4H-SiC MOSFETs. IEEE Transactions on Electron Devices, 2005, 52, 1954-1962.	3.0	41

#	Article	IF	Citations
235	1330 V, 67 m/spl Omega//spl middot/cm/sup 2/ 4H-SiC(0001) RESURF MOSFET. IEEE Electron Device Letters, 2005, 26, 649-651.	3.9	33
236	Growth of Nonpolar AlN and AlGaN on 4H-SiC (1-100) by Molecular Beam Epitaxy. Materials Research Society Symposia Proceedings, 2005, 892, 638.	0.1	2
237	Towards High-Quality AlN/SiC Hetero-Interface by Controlling Initial Processes in Molecular-Beam Epitaxy. Materials Science Forum, 2004, 457-460, 1569-1572.	0.3	5
238	High Channel Mobilities of MOSFETs on Highly-Doped 4H-SiC (11-20) Face by Oxidation in N₂O Ambient. Materials Science Forum, 2004, 457-460, 1429-1432.	0.3	9
239	4H-SiC MOSFETs with a Novel Channel Structure (Sandwiched Channel MOSFET). Materials Science Forum, 2004, 457-460, 1409-1412.	0.3	2
240	Influence of Substrate Misorientation Angle and Direction in Growth of GaN on Off-axis SiC (0001). Materials Research Society Symposia Proceedings, 2004, 831, 654.	0.1	1
241	Molecular beam epitaxy of GaN on lattice-matched ZrB2 substrates using low-temperature GaN and AlN nucleation layers. Materials Research Society Symposia Proceedings, 2004, 831, 660.	0.1	0
242	Molecular-beam epitaxy of III-N on novel ZrB 2 substrates. , 2004, , .		0
243	SiC Lateral Super-Junction Diodes Fabricated by Epitaxial Growth. Materials Science Forum, 2003, 433-436, 859-862.	0.3	0
244	Either step-flow or layer-by-layer growth for AlN on SiC (0001) substrates. Materials Research Society Symposia Proceedings, 2003, 798, 377.	0.1	2
245	Surface Control of ZrB2 (0001) Substrate for Molecular-Beam Epitaxy of GaN. Materials Research Society Symposia Proceedings, 2003, 798, 209.	0.1	1
246	High-Quality AlN by Initial Layer-by-Layer Growth on Surface-Controlled 4H-SiC(0001) Substrate. Japanese Journal of Applied Physics, 2003, 42, L445-L447.	1.5	52
247	ZrB2Substrate for Nitride Semiconductors. Japanese Journal of Applied Physics, 2003, 42, 2260-2264.	1.5	22
248	Effects of 6H-SiC surface reconstruction on lattice relaxation of AlN buffer layers in molecular-beam epitaxial growth of GaN. Applied Physics Letters, 2002, 81, 5141-5143.	3.3	16
249	Molecular-beam epitaxial growth of insulating AlN on surface-controlled 6Hâ€“SiC substrate by HCl gas etching. Applied Physics Letters, 2002, 80, 76-78.	3.3	34
250	Growth of AlN $(11ar{2}0)$ on 6H-SiC $(11ar{2}0)$ by Molecular-Beam Epitaxy. Japanese Journal of Applied Physics, 2002, 41, L1348-L1350.	1.5	38
251	Scanning Capacitance and Spreading Resistance Microscopy of SiC Multiple-pn-Junction Structure. Japanese Journal of Applied Physics, 2002, 41, L40-L42.	1.5	12
252	Heteroepitaxial Growth of Insulating AlN on 6H-SiC by MBE. Materials Science Forum, 2002, 389-393, 1457-1460.	0.3	1

#	Article	IF	Citations
253	Scanning Capacitance Microscopy of SiC Multiple PN Junction Structure Grown by Cold-Wall Chemical Vapor Deposition. Materials Science Forum, 2002, 389-393, 659-662.	0.3	1
254	Lattice Relaxation of AlN Buffer on Surface-Treated SiC in Molecular-Beam Epitaxy for Growth of High-Quality GaN. Materials Research Society Symposia Proceedings, 2002, 743, L4.6.1.	0.1	0
255	Lattice relaxation process of AlN growth on atomically flat 6H-SiC substrate in molecular beam epitaxy. Journal of Crystal Growth, 2002, 237-239, 1012-1016.	1.5	20
256	Zirconium Diboride (0001) as an Electrically Conductive Lattice-Matched Substrate for Gallium Nitride. Japanese Journal of Applied Physics, 2001, 40, L1280-L1282.	1.5	94
257	Growth of Cubic GaN by Metal Organic Molecular Beam Epitaxy.. Shinku/Journal of the Vacuum Society of Japan, 2000, 43, 512-517.	0.2	0
258	Selective Area Growth of Cubic GaN on 3C-SiC (001) by Metalorganic Molecular Beam Epitaxy. Japanese Journal of Applied Physics, 2000, 39, L1081-L1083.	1.5	8
259	GaP/Si Heterojunction with Ohmic Conduction Fabricated by Wafer Fusion Technique. Japanese Journal of Applied Physics, 2000, 39, L905-L907.	1.5	1
260	Growth evolution of cubic-GaN on sapphire (0001) substrate by metalorganic molecular beam epitaxy. Journal of Crystal Growth, 1999, 201-202, 437-440.	1.5	11
261	Optical properties of light-hole excitons in ZnSSe/ZnMgSSe tensile-strained quantum wells. Journal of Crystal Growth, 1998, 184-185, 863-866.	1.5	2
262	Hydrogen sulfide treatment of GaAs substrate and its effects on initial stage of ZnSe growth. Journal of Crystal Growth, 1997, 175-176, 593-597.	1.5	2
263	Surface Reconstruction and Morphology of Hydrogen Sulfide Treated GaAs (001) Substrate. Materials Research Society Symposia Proceedings, 1996, 448, 15.	0.1	0
264	Growth of P-type Znse by metalorganic molecular beam epitaxy using metal Zn and dimethylselenide. Journal of Electronic Materials, 1996, 25, 223-227.	2.2	4
265	Dynamics of dense excitonic systems in ZnSe-based single quantum wells. Journal of Crystal Growth, 1996, 159, 814-817.	1.5	0
266	(2 Ã— 6) Surface Reconstruction of GaAs (001) Obtained by Hydrogen Sulfide Irradiation. Japanese Journal of Applied Physics, 1996, 35, L1498-L1500.	1.5	4
267	Growth of ZnSe/ZnMgSSe quantum well structures by metalorganic molecular beam epitaxy under in situ observation of reflection high energy electron diffraction intensity oscillation. Journal of Crystal Growth, 1995, 150, 738-742.	1.5	3
268	Time-resolved nonlinear luminescence of biexcitons in ZnSe-ZnxMg1â^'xSySe1â^'ysingle quantum wells. Physical Review B, 1995, 52, R2289-R2292.	3.2	32
269	Optical Properties of ZnSe/ZnMgSSe Single Quantum Wells Grown by Metalorganic Molecular Beam Epitaxy. Japanese Journal of Applied Physics, 1994, 33, L986-L989.	1.5	15
270	Gas-Source Molecular Beam Epitaxial Growth of (Zn, Mg)(S, Se) Using Bis-methylcyclopentadienyl-magnesium and Hydrogen Sulfide. Japanese Journal of Applied Physics, 1994, 33, L290-L293.	1.5	16

#	Article	IF	Citations
271	Accurate Measurements of Second-Order Nonlinear-Optical Coefficients of Silicon Carbide. Materials Science Forum, 0, 615-617, 315-318.	0.3	1
272	Improved On-Current of 4H-SiC MOSFETs with a Three-Dimensional Gate Structure. Materials Science Forum, 0, 615-617, 753-756.	0.3	0
273	Improved Current Gain in GaN/SiC Heterojunction Bipolar Transistors by Insertion of Ultra-Thin AlN Layer at Emitter-Junction. Materials Science Forum, 0, 615-617, 979-982.	0.3	5
274	1.5 kV Lateral Double RESURF MOSFETs on 4H-SiC (000-1)C Face. Materials Science Forum, 0, 615-617, 757-760.	0.3	2
275	SiC Heterojunction Bipolar Transistors with AlN/GaN Short-Period Superlattice Widegap Emitter. Materials Science Forum, 0, 645-648, 1029-1032.	0.3	0
276	Defect Control in Growth and Processing of 4H-SiC for Power Device Applications. Materials Science Forum, 0, 645-648, 645-650.	0.3	11
277	In-Grown Stacking Faults Identified in 4H-SiC Epilayers Grown at High Growth Rate. Materials Science Forum, 0, 645-648, 287-290.	0.3	1
278	Temperature and Injection Level Dependencies of Carrier Lifetimes in p-Type and n-Type 4H-SiC Epilayers. Materials Science Forum, 0, 645-648, 199-202.	0.3	3
279	Electrical Characterization and Reliability of Nitrided-Gate Insulators for N- and P-Type 4H-SiC MIS Devices. Materials Science Forum, 0, 645-648, 825-828.	0.3	2
280	Impact of Carrier Lifetimes on Non-Destructive Mapping of Dislocations in 4H-SiC Epilayers. Materials Science Forum, 0, 679-680, 302-305.	0.3	1
281	Improved Characteristics of SiC MOSFETs by Post-Oxidation Annealing in Ar at High Temperature. Materials Science Forum, 0, 679-680, 445-448.	0.3	5
282	On the Formation of Intrinsic Defects in 4H-SiC by High Temperature Annealing Steps. Materials Science Forum, 0, 717-720, 247-250.	0.3	4
283	Doping-Induced Lattice Mismatch and Misorientation in 4H-SiC Crystals. Materials Science Forum, 0, 717-720, 481-484.	0.3	25
284	Persistent Photoconductivity in p-Type 4H-SiC Bulk Crystals. Materials Science Forum, 0, 740-742, 413-416.	0.3	1
285	Temperature Dependence of Impact Ionization Coefficients in 4H-SiC. Materials Science Forum, 0, 778-780, 461-466.	0.3	25
286	Ultrahigh-Voltage (> 20 kV) SiC PiN Diodes with a Space-Modulated JTE and Lifetime Enhancement Process via Thermal Oxidation. Materials Science Forum, 0, 778-780, 832-835.	0.3	15
287	Designing of Quasi-Modulated Region in 4H-SiC Lateral RESURF MOSFETs. Materials Science Forum, 0, 778-780, 943-946.	0.3	1
288	Identification of the Negative Carbon Vacancy at Quasi-Cubic Site in 4H-SiC by EPR and Theoretical Calculations. Materials Science Forum, 0, 778-780, 285-288.	0.3	0

#	Article	IF	Citations
289	High-Temperature Operation of Electrostatically-Excited Single-Crystalline 4H-SiC Microcantilever Resonators. Materials Science Forum, 0, 821-823, 914-918.	0.3	1
290	ESR Study on Hydrogen Passivation of Intrinsic Defects in p-Type and Semi-Insulating 4H-SiC. Materials Science Forum, 0, 858, 318-321.	0.3	2
291	Electron Injection from GaN to SiC and Fabrication of GaN/SiC Heterojunction Bipolar Transistors. Materials Science Forum, 0, , 1545-1548.	0.3	0
292	Increase in net donor concentration due to introduction of donor-like defects by ultra-low-dose Si-ion implantation and subsequent annealing in homoepitaxial n-type GaN. Applied Physics Express, 0, , .	2.4	1
293	Suppression of cluster formation in GaN growth by tri-halide vapor phase epitaxy with external GaCl₃ gas supply system. Japanese Journal of Applied Physics, 0, , .	1.5	1